

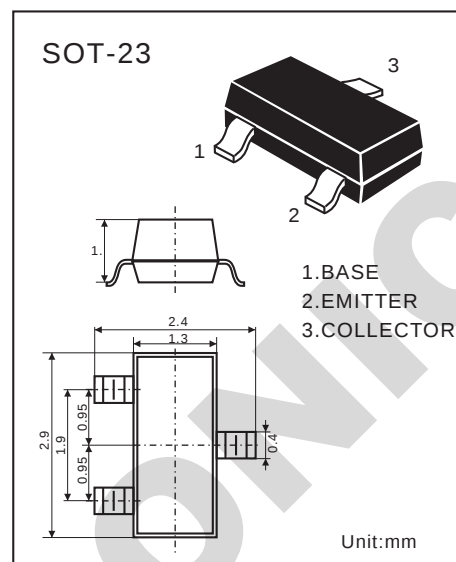
PNP EPITAXIAL SILICON TRANSISTOR

1W OUTPUT AMPLIFIER OF PORTABLE
RADIOS IN CLASS
B PUSH-PULL OPERATION

Complement to 9013G

Collector Current :I_c=-500mA

High Total Power Dissipation P_c=225mW



ABSOLUTE MAXIMUM RATINGS

(T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-500	mA
Collector Dissipation T _a =25°C*	P _D	225	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55~150	°C

Electrical Characteristics

(T_a=25°C)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Condition
Collector-Base Breakdown Voltage	BV _{CB0}	-40			V	I _C =-100μA I _E =0
Collector-Emitter Breakdown Voltage#	BV _{CEO}	-20			V	I _C =-1mA I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E =-100μA I _C =0
Collector-Base Cutoff Current	I _{CB0}			-100	nA	V _{CB} =-25V, V _C =0
Emitter-Base Cutoff Current	I _{EBO}			-100	nA	V _{CB} =-3V, I _C =0
DC Current Gain	H _{FE1}	64	120	300		V _{CE} =-1V, I _C =-50mA
DC Current Gain	H _{FE2}	30				V _{CE} =-1V, I _C =-500mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.18	-0.6	V	I _C =-500mA, I _B =-50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}		-0.95	-1.2	V	I _C =-500mA, I _B =-50mA
Base-Emitter On Voltage	V _{BE(on)}	-0.6	-0.67	-0.7	V	V _{CE} =-1V, I _C =-10mA

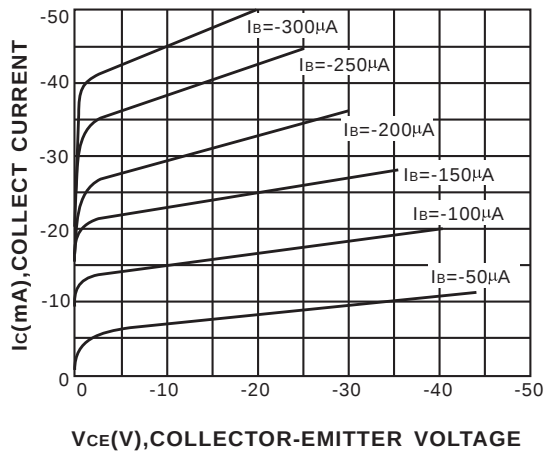
*Total Device Dissipation:FR=1X0.75X0.062 in Board Derate 25°C

#Pulse Test: Pulse Width≤300uS Duty cycle ≤2%

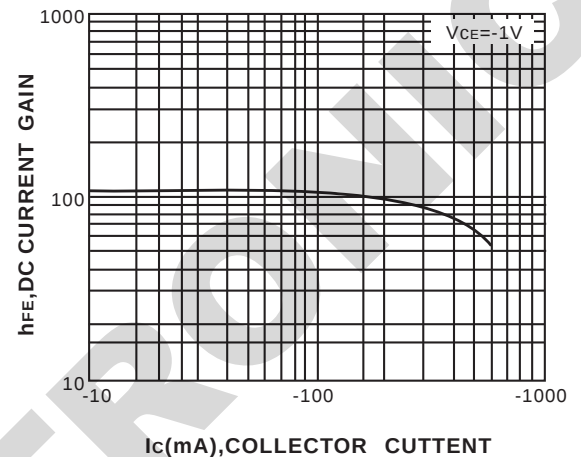
DEVICE MARKING:

9012=J6

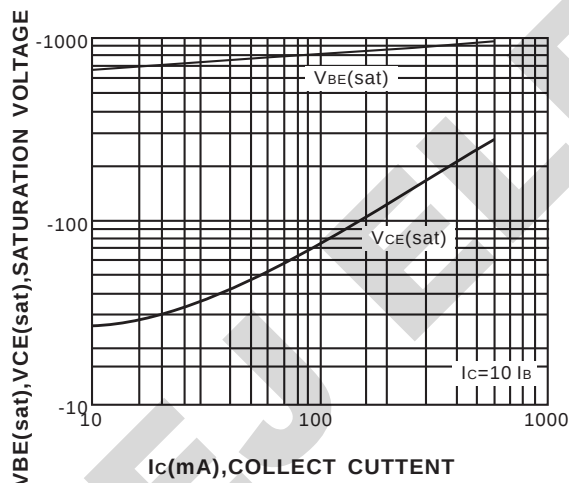
Typical Characteristics



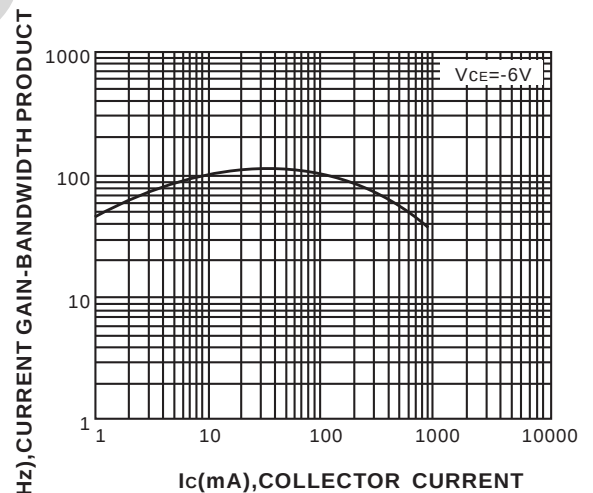
Static Characteristic



DC Current Gain



Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



Current Gain Bandwidth Product